

Supplementary Material

of

Tunable electronic band structure of $\text{AlP}_3/\text{Cs}_3\text{Bi}_2\text{I}_6\text{Cl}_3$ van der Waals heterostructure induced by electric field: a first-principles study

Cheng-sheng Liao^a, Lin Lang^a, Qiu-yi Wang^a, Yu-qing Zhao^b, Zhuo-liang

Yu^{a,*}

^a *Key Laboratory of Hunan Province on Information Photonics and
Freespace Optical Communications, School of Physics and Electronics
Science, Hunan Institute of Science and Technology, Yueyang 414006,
People's Republic of China*

^b *School of Physics and Electronics Science, Hunan University of Science
and Technology, Xiangtan 411201, People's Republic of China*

E-mail: 12021016@hnist.edu.cn

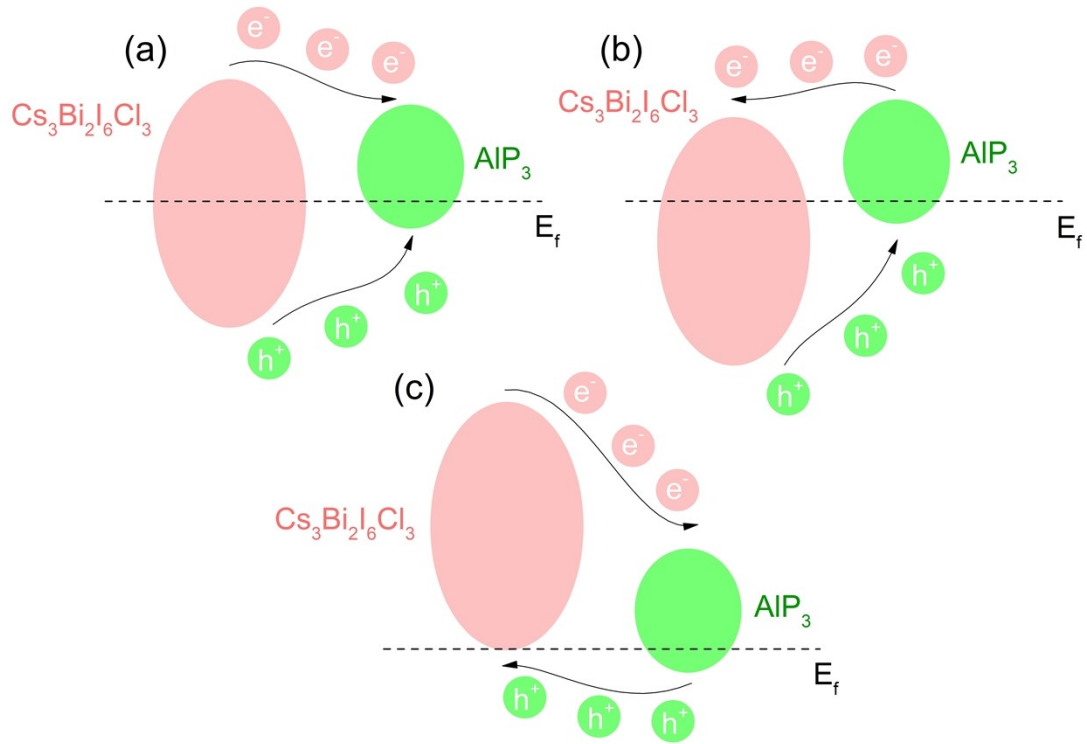


Figure S1 Schematic illustration of the band alignment of $\text{AIP}_3/\text{Cs}_3\text{Bi}_2\text{I}_6\text{Cl}_3$ vdWH under an external electric field of (a) 0 V/\AA , (b) 0.1 V/\AA and (c) 0.2 V/\AA , respectively

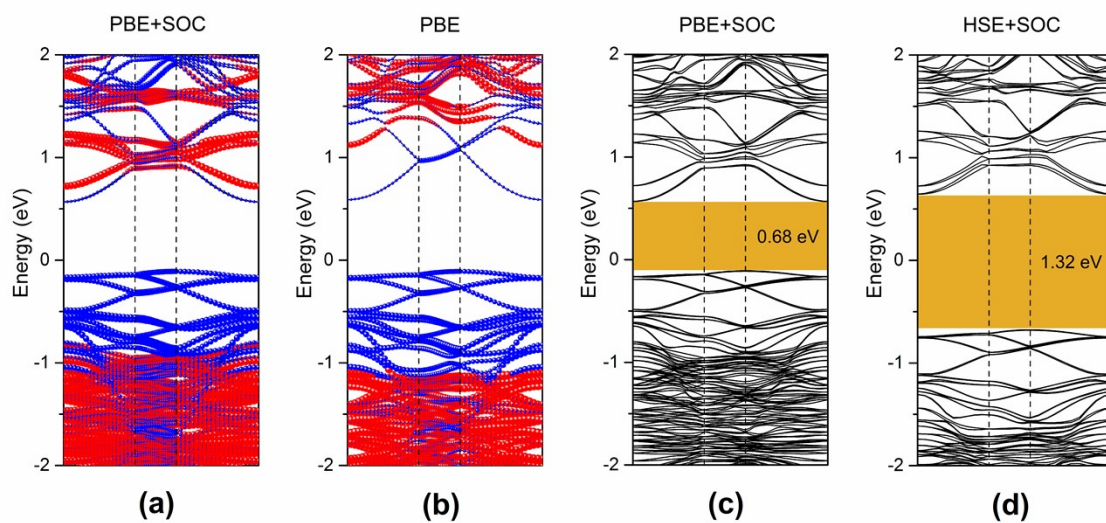


Figure S2 (a) The projected band structure of $\text{AlP}_3/\text{Cs}_3\text{Bi}_2\text{I}_6\text{Cl}_3$ vdWH calculated by PBE+SOC functional. (b) The projected band structure of $\text{AlP}_3/\text{Cs}_3\text{Bi}_2\text{I}_6\text{Cl}_3$ vdWH calculated by PBE functional. (c) The electronic band structure of $\text{AlP}_3/\text{Cs}_3\text{Bi}_2\text{I}_6\text{Cl}_3$ vdWH calculated by PBE+SOC functional. (d) The electronic band structure of $\text{AlP}_3/\text{Cs}_3\text{Bi}_2\text{I}_6\text{Cl}_3$ vdWH calculated by HSE+SOC functional.

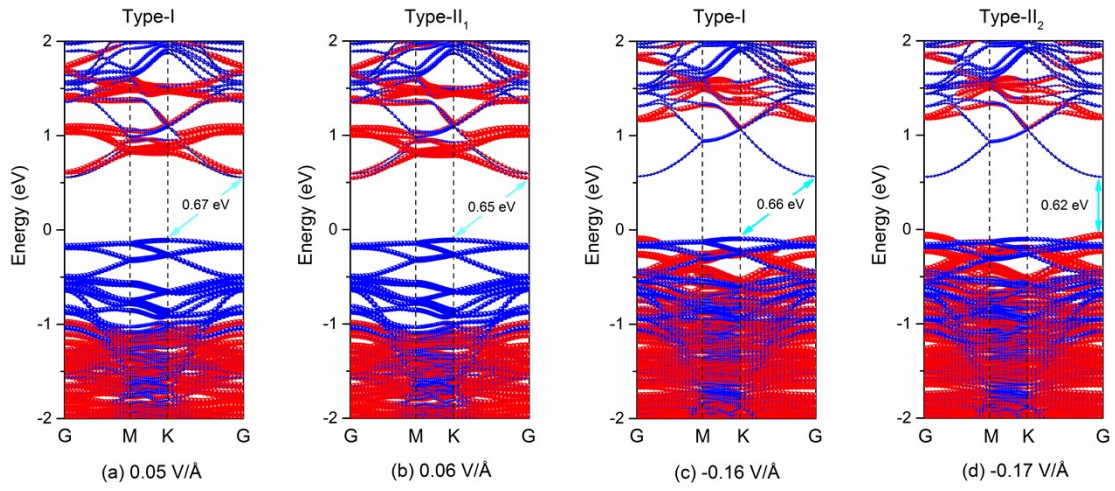


Figure S3. The electronic band structures under external electric fields of (a) 0.05 V/\AA , (b) 0.06 V/\AA , (c) -0.16 V/\AA and (d) -0.17 V/\AA for $\text{AlP}_3/\text{Cs}_3\text{Bi}_2\text{I}_6\text{Cl}_3$ vdWH. The Fermi level is set to zero.